

Specification for Approval

DEVICE NUMBER: BIR-BM13E4G-2

• CUSTOMER:

SAMPLES ATTACHED AREA

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FOR CUSTOMER'S APPROVAL STAMP OR SIGNATURE

APPROVED	PURCHASE	MANUFACTURE	QUALITY	ENGINEERING
A				
7	7			

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ISSUED	APPROVED	PREPARED		
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BIR-BM13E4G-2

END-LOOK PACKAGE LIGHT EMITTING DIODE

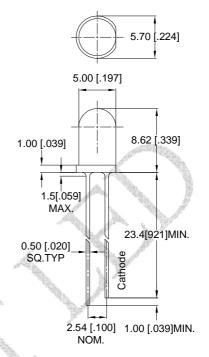
I Features:

- 1. High radiant power and high radiant intensity.
- 2. Standard T-1 3/4(5mm)package.
- 3. Peak wavelength λp=940nm.
- 4. Good spectral matching to si-photodetector.
- 5. Radiant angle: 40°
- 6. Lens Appearance: Water Clear.
- 7.This product doesn't contain restriction substance, comply RoHS standard

Applications:

- 1. Remote Control.
- 2. Automatic Control System.

Package Dimensions:



NOTES:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is ±0.25mm (0.01') unless otherwise specified.
- 3. Lead spacing is measured where the leads emerge from the package.
- 4. Specifications are subject to change without notice.

I Absolute Maximum Ratings(Ta=25℃)

Parameter	Symbol	Rating	Unit
Power Dissipation	Pd	150	mW
Continuous Forward Current	I _F	100	mA
Peak Forward Current *1	I _{FP}	1.0	А
Reverse Voltage	V _R	5	V
Operating Temperature	Topr	-40°C ~85°C	-
Storage Temperature	Tstg	-45°C ~85°C	-

^{*1 (300}pps 10us pulse)

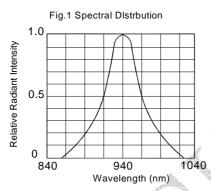


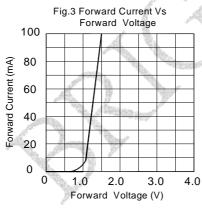
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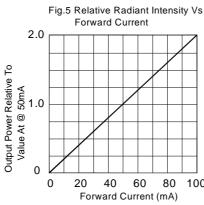
I Optical- Electrical Characteristics (Ta=25°C)

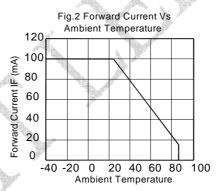
Parameter	Symbol	Test Conditions	Min	TYP	Max	Unit
Radiant Intensity	le	I _F =50mA	9.90	30	-	mW/sr
Forward Voltage	V _F	I _F =50mA	-	1.25	1.5	V
Reverse Current	I _R	V _R =5V	-	-	100	μA
Peak Wavelength	λр	I _F =50mA	-	940	-	nm
Spectral Line Half- Width	Δλ	I _F =50mA	-	50		nm
Viewing Angle	2θ _{1/2}	I _F =20mA	-	40	-	deg

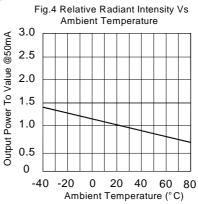
I Typical Optical-Electrical Characteristic Curves

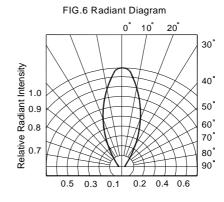








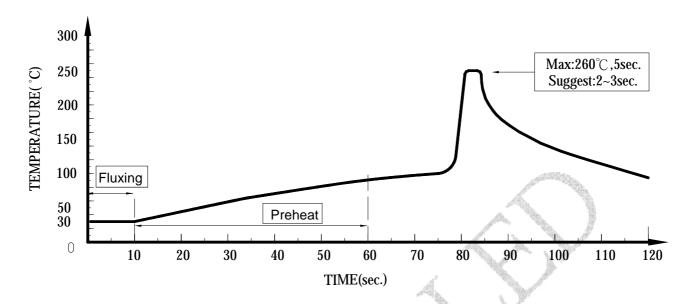






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Dip Soldering



- Please avoid any external stress applied to the lead-frames and epoxy while the LEDs are at high temperature, especially during soldering
- 2. DIP soldering and hand soldering should not be done more than one time.
- 3. After soldering, avoid the epoxy lens from mechanical shock or vibration until the LEDs are back to room temperature.
- 4. Avoid rapid cooling during temperature ramp-down process
- Although the soldering condition is recommended above,soldering at the lowest possible temperature is feasible for the LEDs

■ IRON Soldering

A: Max: 350° C Within 3 sec. One time only.

B: The products of 3mm without flange, welding condition of flat plate PCB Max:

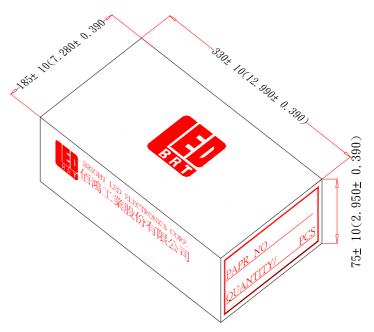
350°C Within 2 sec. One time only

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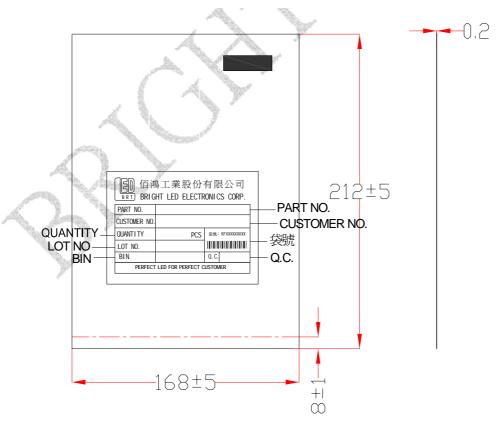


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Tapping and packaging specifications(Units: mm)



I Packaging Bag Dimensions



Notes:

- 1 . 500pcs per bag, 5Kpcs per box.
- 2 · All dimensions are in millimeters(inches).
- 3 · Specifications are subject to change without notice.



BIR-BM13E4G-2

Infrared Emitting Diode Specification

2Commodity: Infrared emitting diode

2Intensity Bin Limits (At 50mA)

BIN CODE	Min.(mW/sr)	Max.(mW/sr)
11	9.90	13.81
12	13.81	19.42
13	19.42	27.20
14	27.20	38.08
15	38.08	53.31
16	53.31	74.63

NOTES: Tolerance of measurement of Radiant Intensity :±15%